



CHENMKO ENTERPRISE CO.,LTD

Lead free devices

**SMALL FLAT
PNP Epitaxial Transistor**

VOLTAGE 50 Volts CURRENT 2 Ampere

2SA1213PT

APPLICATION

* Power amplifier .

FEATURE

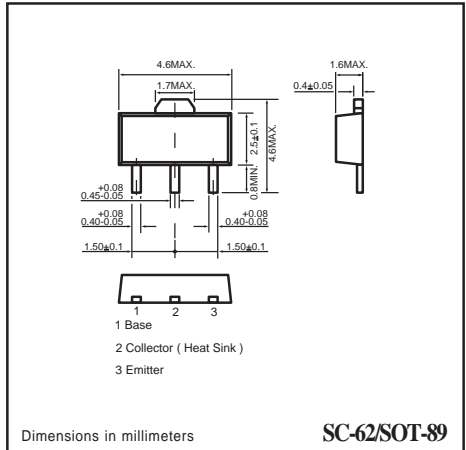
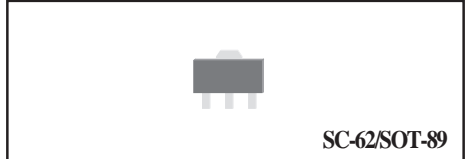
- * Small flat package. (SC-62/SOT-89)
- * Low saturation voltage $V_{CE(sat)} = -0.5V(\text{max.})(I_C = -1A)$
- * High speed switching time: $t_{stg} = 1.0\mu\text{Sec}(\text{typ.})$
- * $PC = 1.0$ to $2.0W$ (mounted on ceramic substrate).
- * High saturation current capability.

CONSTRUCTION

* PNP Switching Transistor

MARKING

- * HFE(O):NO
- * HFE(Y):NY



CIRCUIT



MAXIMUM RATINGS (At $T_A = 25^\circ\text{C}$ unless otherwise noted)

| RATINGS | CONDITION | SYMBOL | MIN. | MAX. | UNITS |
|-------------------------------|--------------------------------------|-----------|------|------|------------------|
| Collector - Base Voltage | Open Emitter | V_{CB0} | - | -50 | Volts |
| Collector - Emitter Voltage | Open Base | V_{CE0} | - | -50 | Volts |
| Emitter - Base Voltage | Open Collector | V_{EB0} | - | -5 | Volts |
| Collector Current DC | | I_C | - | -2 | Amps |
| Peak Collector Current | | I_{CM} | - | -2 | Amps |
| Peak Base Current | | I_{BM} | - | -0.4 | Amps |
| Total Power Dissipation | $T_A \leq 25^\circ\text{C}$; Note 1 | P_{TOT} | - | 1000 | mW |
| Storage Temperature | | T_{STG} | -55 | +150 | $^\circ\text{C}$ |
| Junction Temperature | | T_J | - | +150 | $^\circ\text{C}$ |
| Operating Ambient Temperature | | T_{AMB} | -55 | +150 | $^\circ\text{C}$ |

Note

1. Transistor mounted on ceramic substrate 50mmX50mmX0.8t.
2. Measured at Pulse Width 300 us, Duty Cycle 2%.

2002-10

RATING CHARACTERISTIC CURVES (2SA1213PT)

CHARACTERISTICS (At $T_A = 25^\circ\text{C}$ unless otherwise noted)

| PARAMETERS | CONDITION | SYMBOL | MIN. | TYPE | MAX. | UNITS |
|--------------------------------------|---|-------------|----------|--------|----------|---------------|
| Collector Cut-off Current | $I_E=0; V_{CB}=-50\text{V}$ | I_{CBO} | - | - | -0.1 | μA |
| Emitter Cut-off Current | $I_C=0; V_{EB}=-5\text{V}$ | I_{CEO} | - | - | -0.1 | μA |
| DC Current Gain | $V_{CE}=-2\text{V}$; Note 1 $I_C=-0.5\text{A}$; Note 2 $I_C=-2.0\text{A}$ | h_{FE} | 70 20 | - - | 240 - | |
| Collector-Emitter Saturation Voltage | $I_C=-1\text{A}; I_B=-0.05\text{A}$ | V_{CEsat} | - | - | -0.5 | Volts |
| Base-Emitter Saturation Voltage | $I_C=-1\text{A}; I_B=-0.05\text{A}$ | V_{BEsat} | - | - | -1.2 | mVolts |
| Collector Capacitance | $I_E=I_C=0; V_{CB}=10\text{V}$; $f=1\text{MHz}$ | C_C | - | 40 | - | pF |
| Transition Frequency | $I_C=-0.5\text{A}; V_{CE}=-2\text{V}$; $f=100\text{MHz}$ | f_T | - | 120 | - | MHz |

SWITCHING TIMES (Between 10% and 90% levels)

| PARAMETERS | CONDITION | SYMBOL | MIN. | TYPE | MAX. | UNITS |
|--------------|-----------|----------|------|------|------|-----------------|
| Turn-on Time | | t_{on} | - | 0.1 | - | μSec |
| Storage Time | | t_s | - | 1.0 | - | μSec |
| Fall Time | | t_f | - | 0.1 | - | μSec |

Note :

1. Pulse test: $t_p \leq 300\mu\text{Sec}$; $\delta \leq 0.02$.
2. $h_{FE}(1)$ Classification O: 70 to 140, Y: 120 to 240

RATING CHARACTERISTIC CURVES (2SA1213PT)

Typical Electrical Characteristics

Figure 1. V_{CE} - I_C

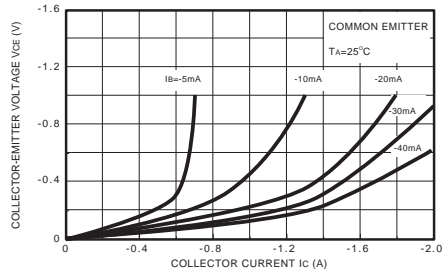


Figure 2. V_{CE} - I_C

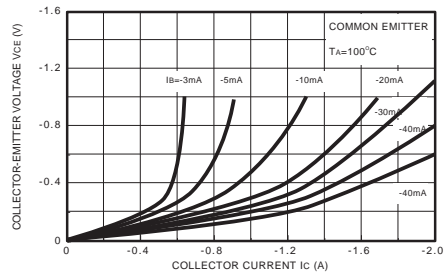


Figure 3. V_{CE} - I_C

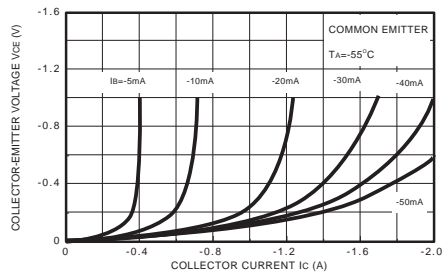


Figure 4. h_{FE} - I_C

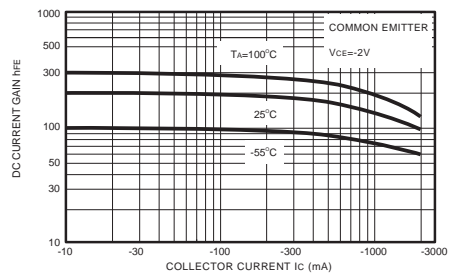


Figure 5. V_{CE(sat)} - I_C

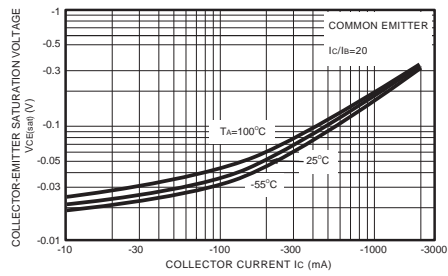
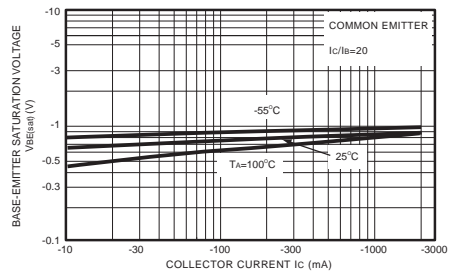


Figure 6. V_{BE(sat)} - I_C



RATING CHARACTERISTIC CURVES (2SA1213PT)

Typical Electrical Characteristics

Figure 7. $I_c - V_{BE}$

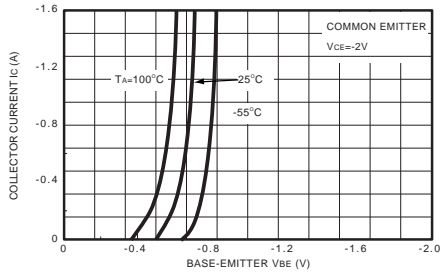


Figure 8. $P_c - T_A$

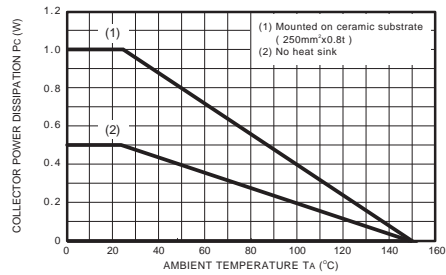


Figure 9. Safe Operation Area

